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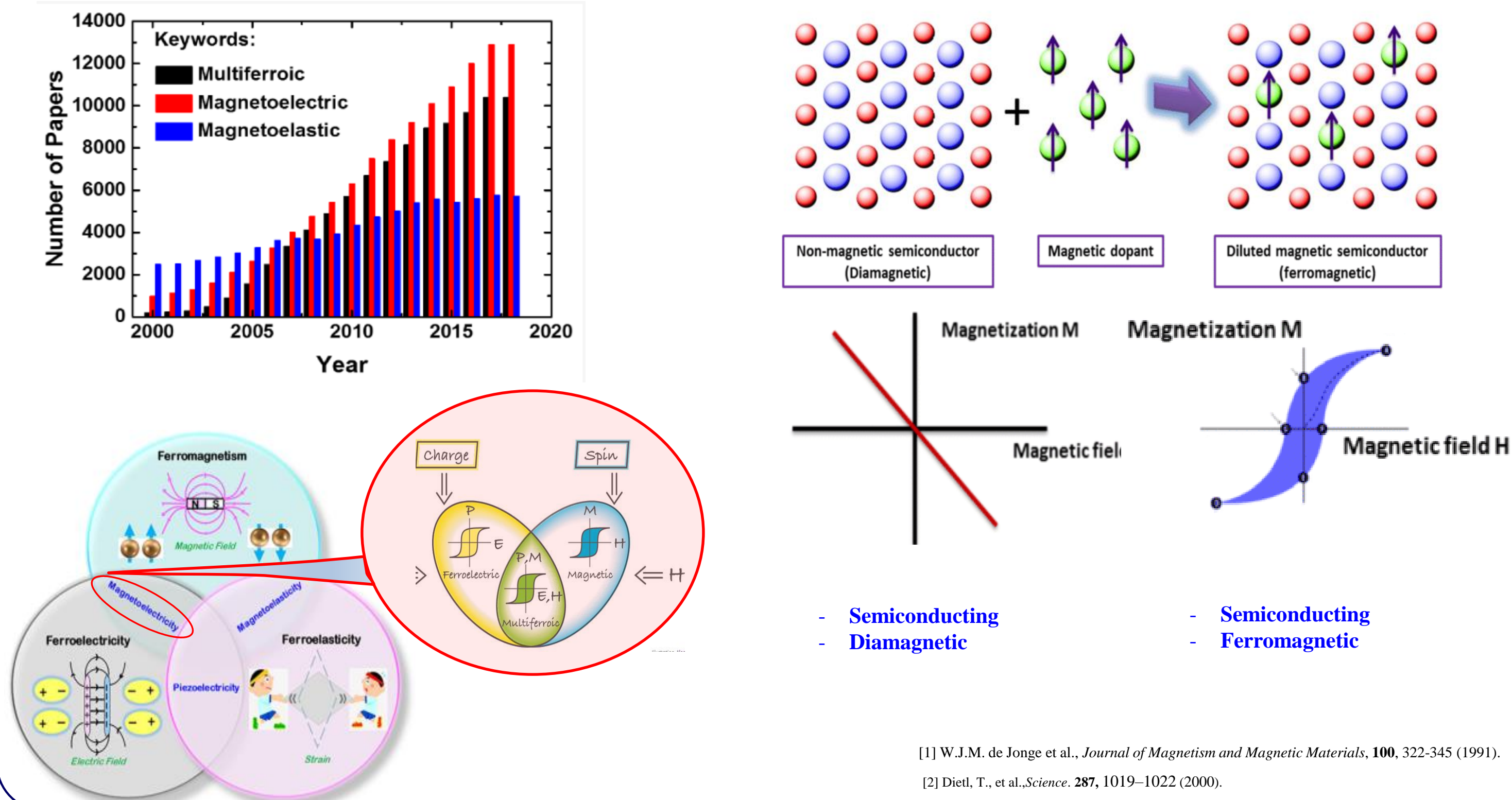
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## Abstract

IV-VI materials doped with magnetic impurities hold potential for spintronic applications particularly by integrating the memory component within the semiconducting matrix. This work intends to investigate the carrier mediated magnetic interactions in GeTe lattice alloyed with Mn ions. We present  $\text{Ge}_{1-x-y}\text{Si}_x\text{Mn}_y\text{Te}$  bulk crystals by altering their chemical composition in the range  $0.056 \leq x \leq 0.10$  and  $0.0036 \leq y \leq 0.046$ . The magnetic phase transition temperature rises from  $T_C = 25$  K to about 160 K for the highest impurity level. The analysis of inverse of susceptibility with modified Curie-Weiss law finds ferromagnetic-like interaction in the alloys. The magnetically glassy samples were interpreted with frequency dependent susceptibility. This identified scaling parameter,  $R = 0.2 - 0.6$  which indicate the formation of clusters in the glassy samples. Finally, the high field magnetization data has been used to calculate the number of active magnetic ions in semiconductor matrix.

## Introduction and Motivation

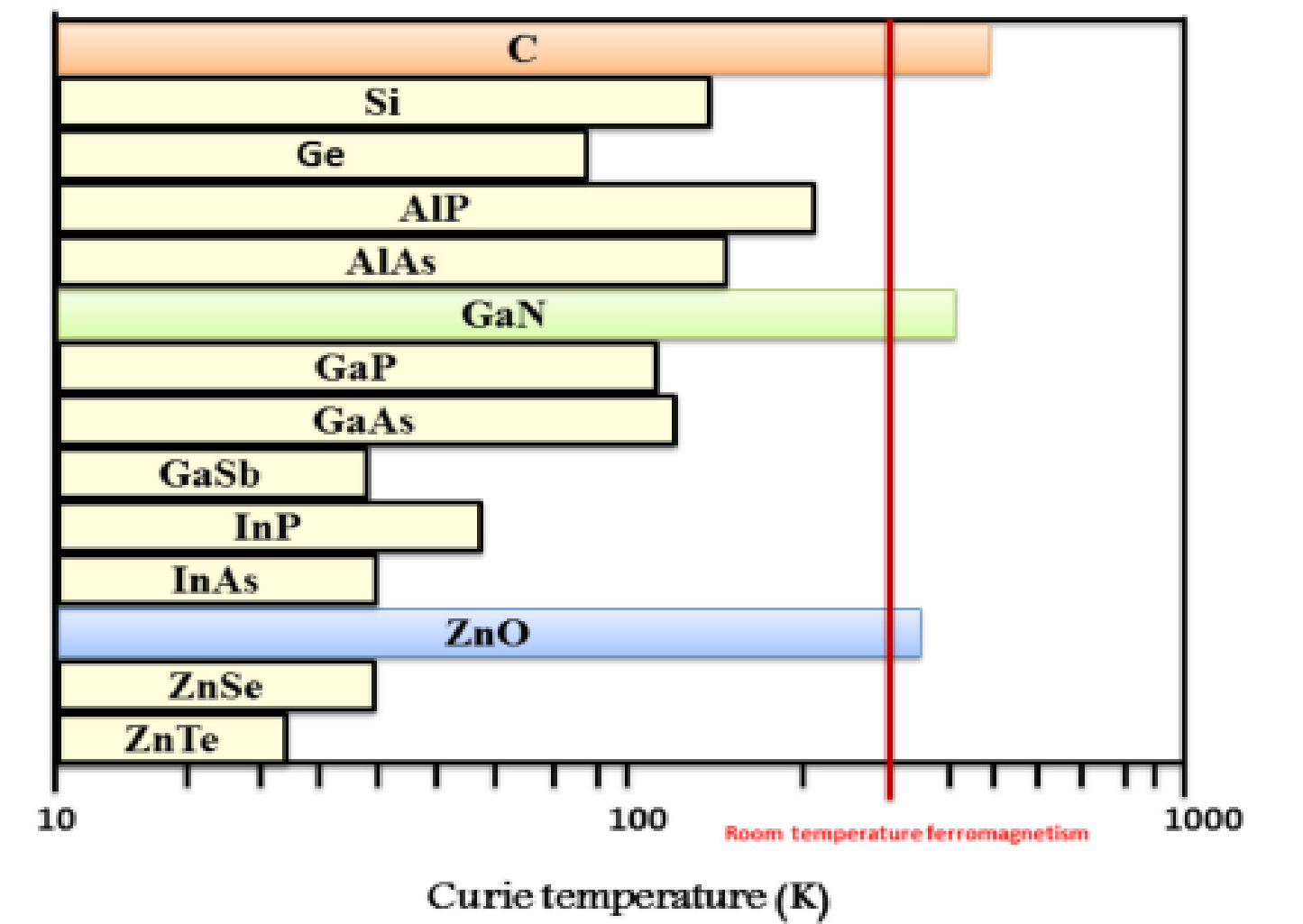
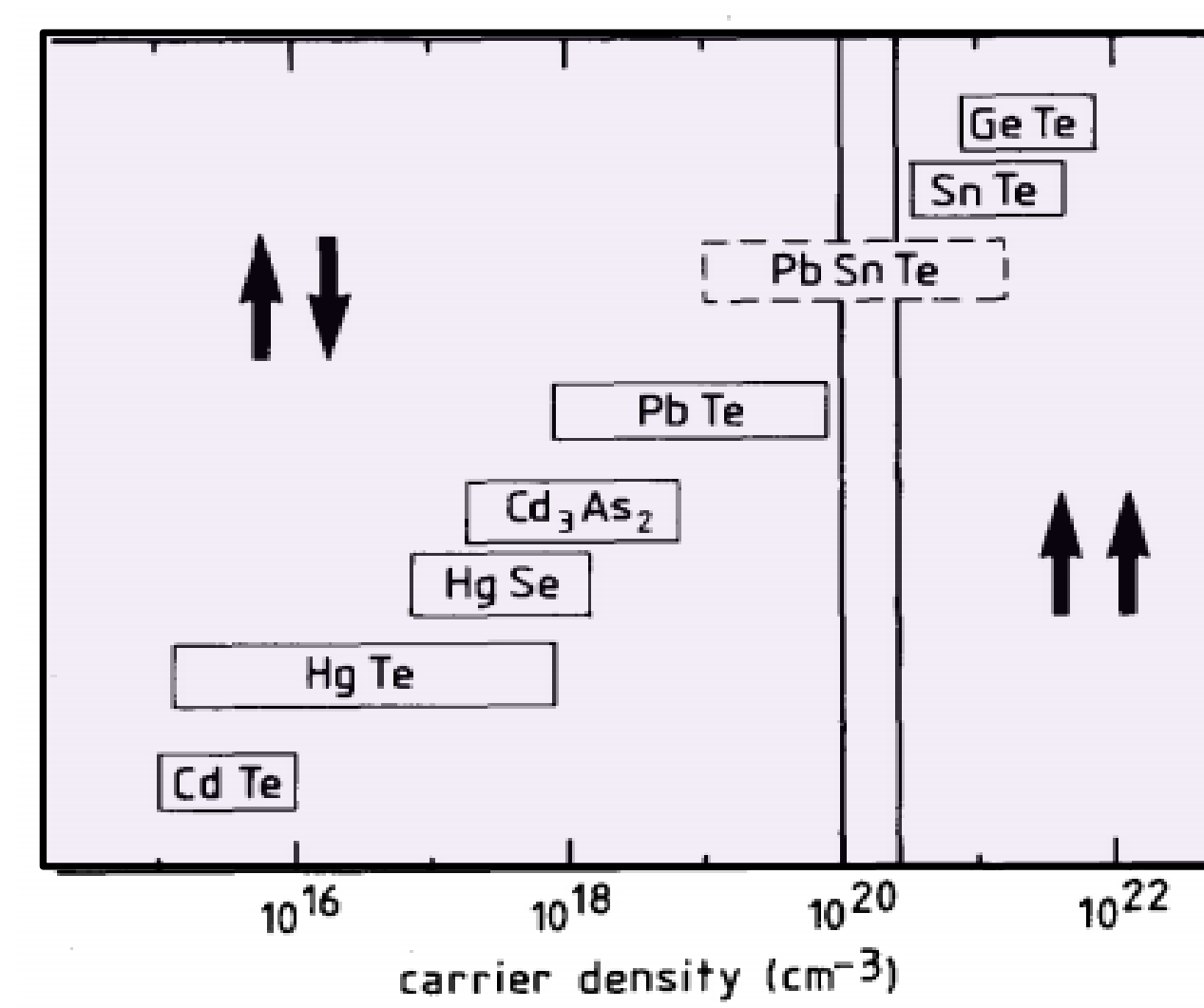
### Why Multiferroics



### Why IV-VI semiconductors

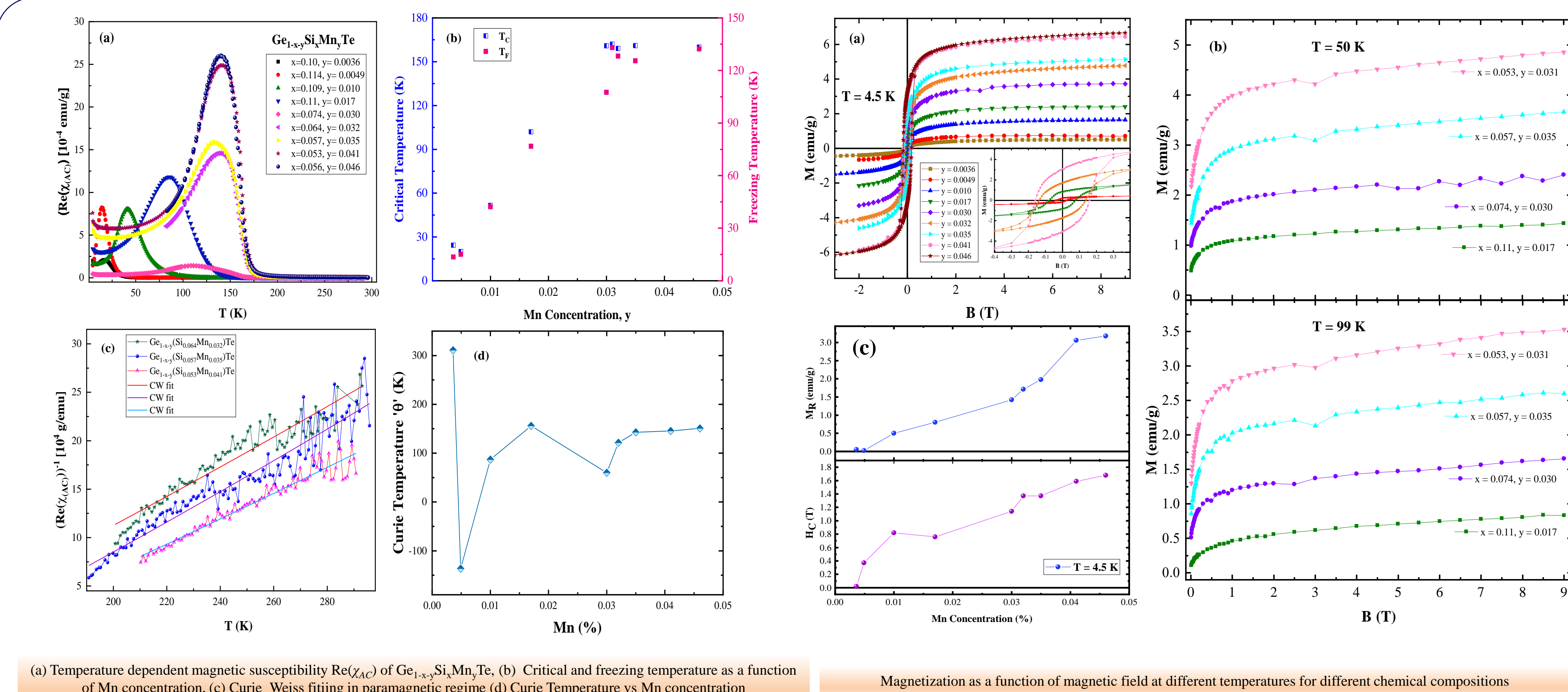
- Magnetic ion concentration
- Magnetic coupling strength

- Curie temperature
- Tailoring properties



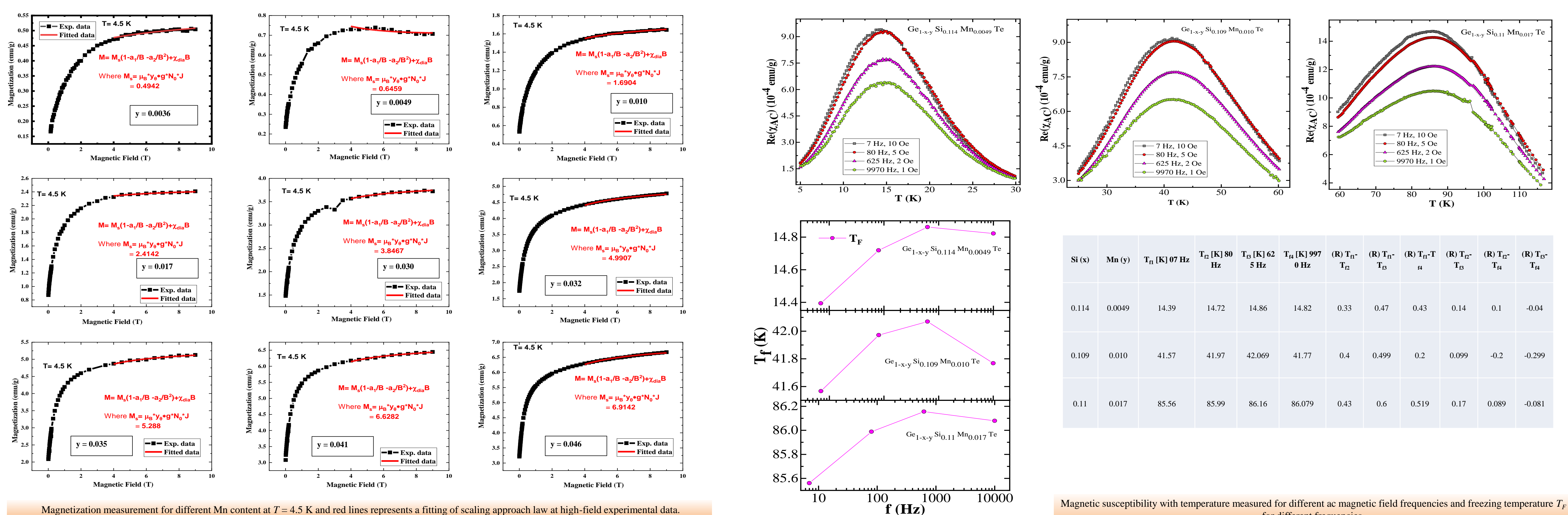
[2] Dietl, T., et al., *Science*, 287, 1019-1022 (2000).

## Results and Discussion



x	y	$y_0$	$\Theta$ [K]	$M_r$ [emu/g] $T=4.5$ K	$H_c$ [T] $T=4.5$ K	$M_{S,app}$ [emu/g] $T=4.5$ K	$M_{S,th}$ [emu/g] $T=4.5$ K
0.10	0.003	0.001	$43.5 \pm 1.3$	0.05	0.2	0.4942	0.5139
0.114	0.0049	0.002	$76.9 \pm 5.3$	0.2	0.3	0.6459	0.7018
0.109	0.010	0.005	$112.8 \pm 15.6$	0.5	0.8	1.6904	1.4313
0.11	0.017	0.007	$139.6 \pm 0.2$	0.8	0.7	2.4142	2.4353
0.074	0.030	0.010	$149.8 \pm 0.3$	1.4	1.1	3.8467	4.2676
0.064	0.032	0.012	$170.2 \pm 3.5$	1.7	1.3	4.99	4.5426
0.057	0.035	0.013	$171.1 \pm 1.3$	2.0	1.3	5.2886	4.9620
0.053	0.041	0.019	$172.8 \pm 0.5$	3.0	1.5	6.6282	5.8104
0.056	0.046	0.018	$174.9 \pm 0.7$	3.1	1.6	6.9146	6.5264

Si content x, Mn content y, effective manganese content  $y_0$ , Curie-Weiss temperature  $\Theta$ , remanence magnetization  $M_r$ , Coercive field  $H_c$  and magnetization saturation  $M_s$  calculated at temperature  $T = 4.5$  K.



Si (x)	Mn (y)	$T_n$ [K] 07 Hz	$T_n$ [K] 80 Hz	$T_n$ [K] 625 Hz	$T_n$ [K] 9970 Hz	(R) $T_{n-}$ $T_n$	(R) $T_{n-}$ $T_n$	(R) $T_{n-}$ $T_n$	(R) $T_{n-}$ $T_n$	(R) $T_{n-}$ $T_n$	(R) $T_{n-}$ $T_n$
0.114	0.0049	14.39	14.72	14.86	14.82	0.33	0.47	0.43	0.14	0.1	-0.04
0.109	0.010	41.57	41.97	42.069	41.77	0.4	0.499	0.2	0.099	-0.2	-0.299
0.11	0.017	85.56	85.99	86.16	86.079	0.43	0.6	0.519	0.17	0.089	-0.081

## Conclusion

In conclusion, we have investigated the magnetic properties of a bulk  $\text{Ge}_{1-x-y}\text{Si}_x\text{Mn}_y\text{Te}$  crystal with a different chemical composition of Mn and Si. The crystal has been examined by temperature dependent magnetic susceptibility and magnetization measurements. Obtained results reveal the transition from paramagnet to ferromagnetic like ordering. The modified Curie-Weiss fitting done in paramagnetic region for analyzing the magnetic ordering and calculate Curie constant and Curie-Weiss temperature. The transition state has further been analyzed by frequency dependent susceptibility measurements. Also, the  $M(H)$  curves having low coercive field attributes the existence of ferromagnetic state and magnetization saturation was estimated by fitting the phenomenological scaling approach law. The results shows that magnetic saturation  $M_s$  values are greatly influenced by changing/increasing the magnetic ion Mn concentration.